

# Gunter Semiconductor GmbH

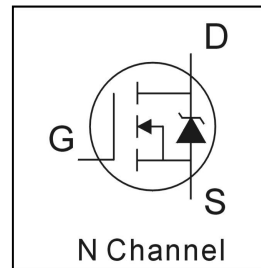
# GFCE50

## N Channel highvoltage , Power MOSFET

### Chip Specification

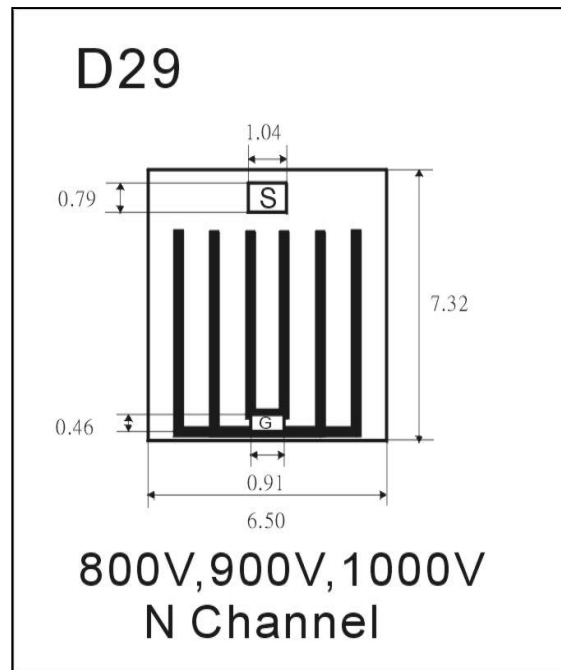
#### General Description:

- \* Advanced Process Technology
- \* Dynamic dV/dt Rating
- \* **150°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**
- \* **High breakdown voltage**



#### Mechanical Data:

D29	
Dimension	6.50mm x 7.32mm
Thickness:	480 μm
Metallization:	
Top :	Al
Backside :	CrNiAg / Au
Suggested Bonding Conditions:	
Die Mounting:	Solder Perform
95/5 PbSn or 92.5./2.5/5 PbAgIn	
Source Bonding Wire:	10 mil Al



#### Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	800	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	1.2	Ω	VGS=10V, ID=4.7A
Continuous Drain current ( in target package)	ID@25°C	5	A	VGS=10V
Continuous Drain current ( in target package)	ID@100°C	3.2	A	VGS=10V
Operation Junction	Tj	-55~150	°C	
Storage Temperature	TSTR	-55~150	°C	

#### Target Device: IRFPE50

TO-247AC

PD

190

W

@Tc=25°C

